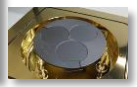
RTP System

REAL RTP series

REAL RTP series

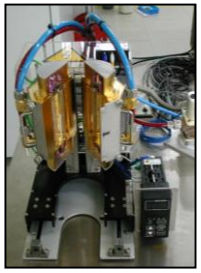
Model	REAL RTP-100	REAL RTP-150	REAL RTP-200
Picture	  	  Zone Control	
Product Sample	Si, Sapphire, Glass, Ceramic, etc.	Si, Sapphire, Glass, Ceramic, etc.	Si, Sapphire, Glass, Ceramic, etc.
Substrate Size	4inch	6inch	8inch
Substrate holder	SiC coated graphite	SiC coated graphite	SiC coated graphite
Temperature Range	150~1,250℃	150~1,250℃	150~1,250℃
Heating Rate	10~200℃/sec	10~150℃/sec	10~150℃/sec
Control Zone	1-zone	3-zone	6-zone
Temperature Uniformity	±3℃	±3℃	±3℃
Temperature Accuracy	±2℃	±2℃	±2℃
Vacuum	Standard : 5.0E-3 Torr Option : 1.0E-6 Torr	Standard : 5.0E-3 Torr Option : 1.0E-6 Torr	Standard : 5.0E-3 Torr Option : 1.0E-6 Torr
Gas Supply	3 channels (Extensible)	3 channels (Extensible)	3 channels (Extensible)
Control	PC control	PC control	PC control

Various RTP System

▶ Tube Type RTP

Product sample	Si, Sapphire, Glass, Ceramic, etc.
Substrate size	Piece
Temperature range	150~1,200℃
Control zone	1-zone
Application	Graphene CVD Silicon nano wire growing Carbon nano tube CVD SIC epitaxy

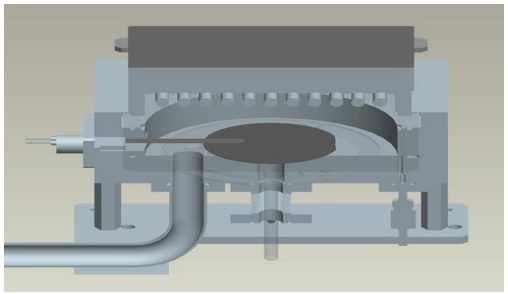
▶ Mini Type RTP

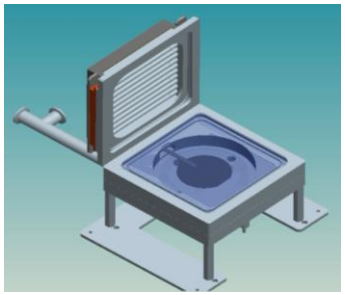


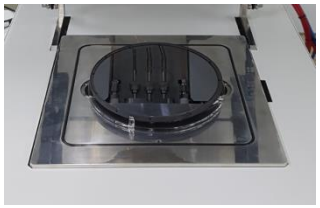
Product sample	Optical fiber, Metal wire, Si, Sapphire, Glass, Ceramic, etc.
Substrate size	Piece
Temperature range	150~1,000℃
Control zone	1-zone
Vacuum	Standard - ATM
	Option - 5.0E-3Torr
Application	Evaluate Tensile strength by temperature in testing tensile strength of optical fiber
Advantage	Low cost, Fast heating, Fast cool down, Desk top style, good for R&D purpose, Rapid heating and cooling available using halogen lamp

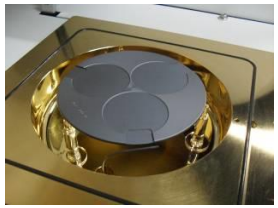
REAL RTP

= REAL T/C Kit + RTP System







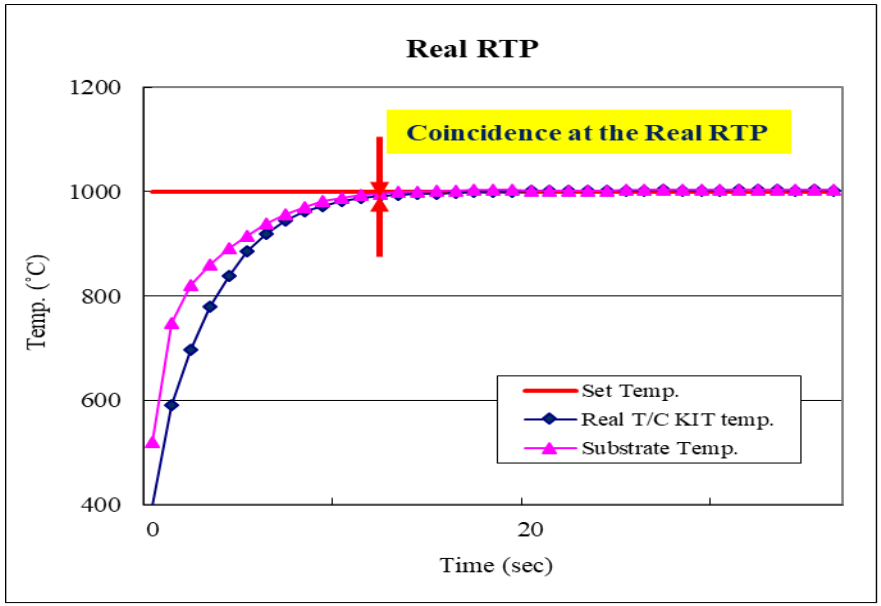


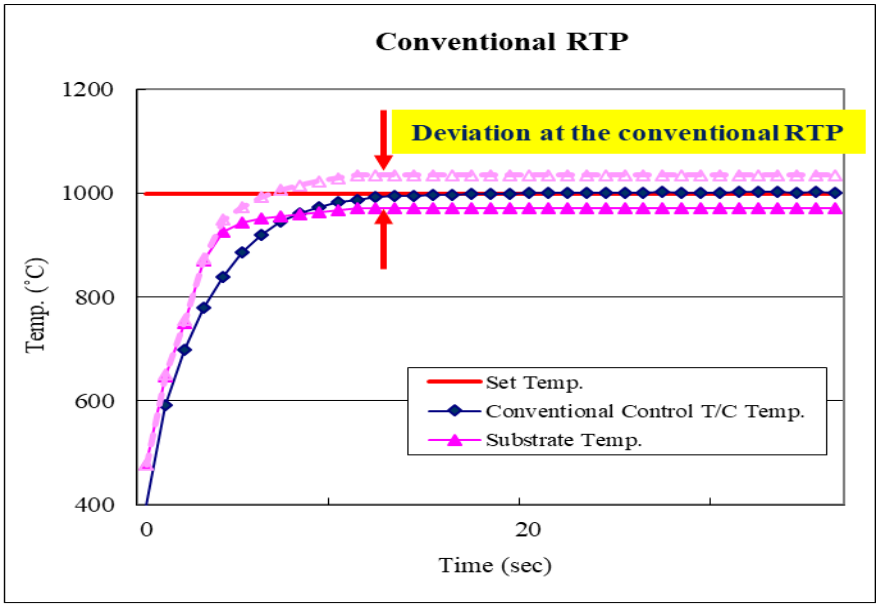
REAL T/C KIT for Si wafer

REAL T/C KIT for Sapphire wafer

REAL RTP Advantage

- Real substrate temperature
- Accurate temperature control
- Unnecessary compensation
- High reliability
- Low cost



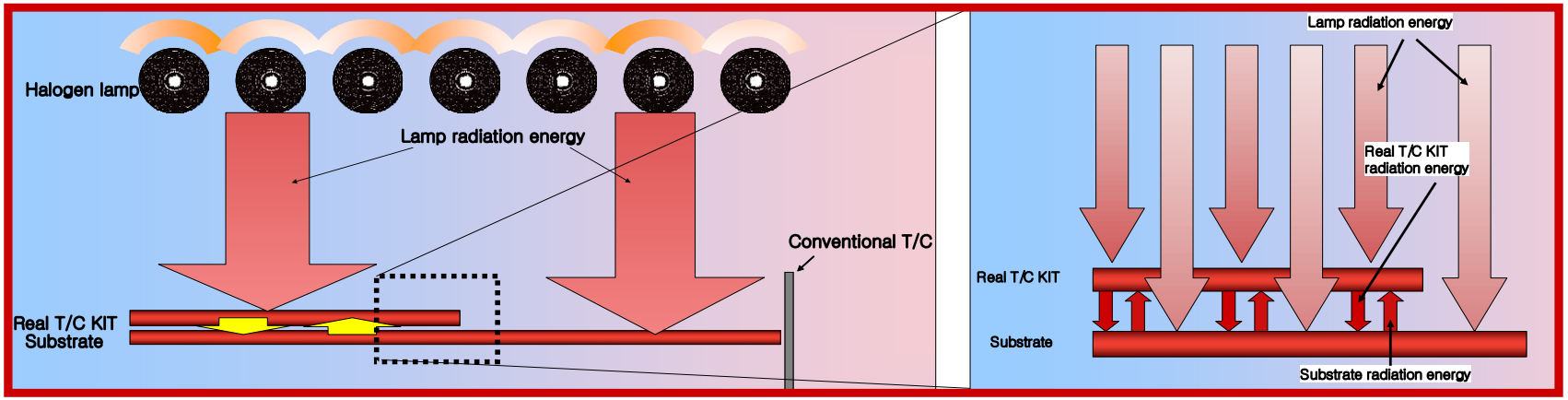


Extremely high precision is required to accurately and reliably temperature of the sample

Deviation at the typically RTP by the environment & the situation → compensation is needed

REAL RTP Advantage

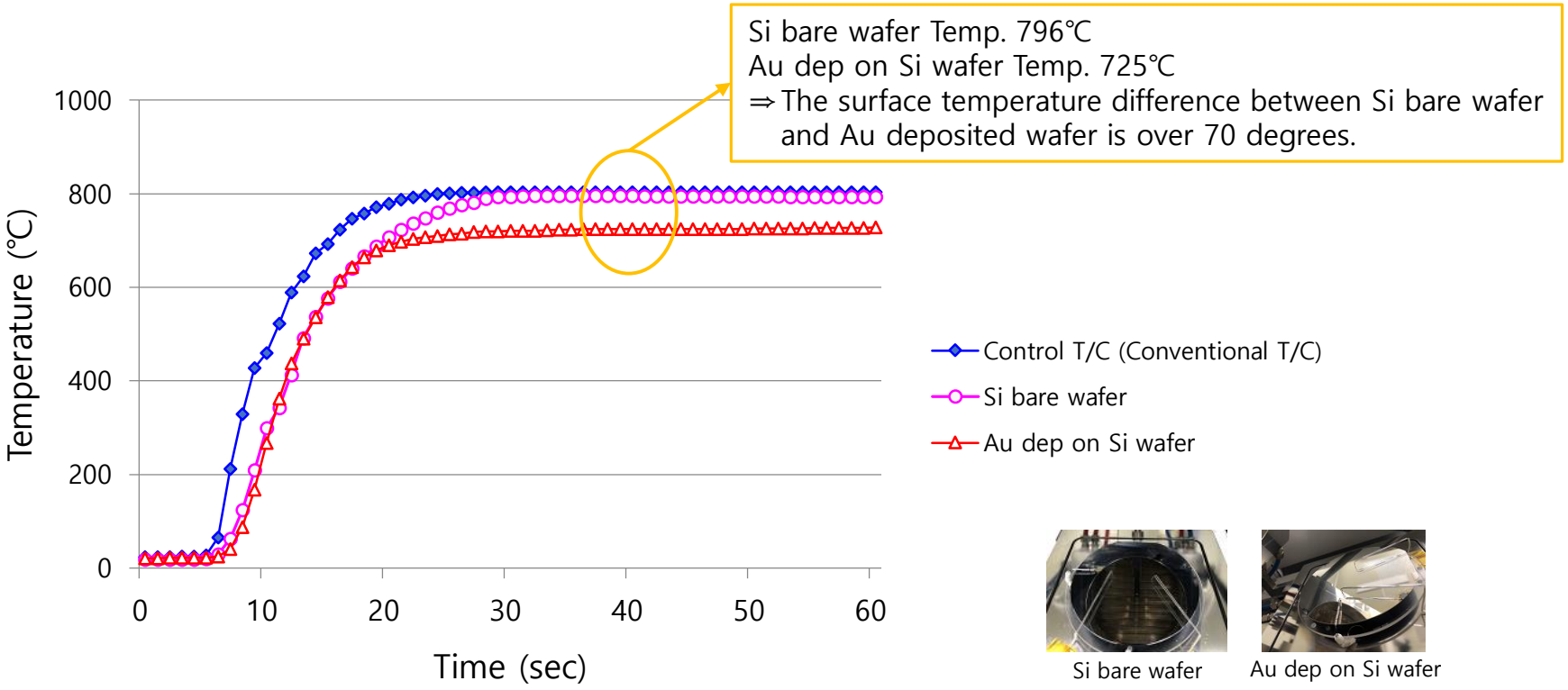
When the halogen lamp is heated by the temperature controller in a PID way to reach set temp, radiant energy of the lamp is released, which leads to heat substrate and the real TC KIT, radiant energy released from the heated substrate is additionally heated, by repeating all this process, finally temperature of substrate and the real TC KIT becomes equal.



REAL RTP Advantage

Using a conventional T/C, the real temperature of Au-deposited wafers that you have to heat to 800 degrees is actually not 800 degrees.

REAL T/C KIT with the same material as the actual wafer(substrate) to be used for real-time accurate temperature control is possible.



Si bare wafer

Au dep on Si wafer